N-Channel 30-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
30	0.050 @ V_{GS} = 10 V	3.4
	0.085 @ V_{GS} = 4.5 V	2.6

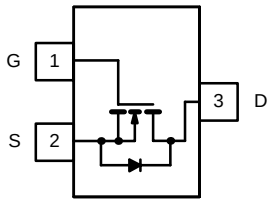
FEATURES

- TrenchFET® Power MOSFET

APPLICATIONS

- Battery Switch

TO-236
(SOT-23)



Top View
Si2316DS (C6)*
*Marking Code

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	5 sec	Steady State	Unit
Drain-Source Voltage		V_{DS}	30		V
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current (T_J = 150°C)[a, b]	T_A= 25°C	I_D	3.4	2.9	A
	T_A= 70°C		2.7	2.3	
Pulsed Drain Current[b]		I_{DM}	16		
Continuous Source Current (Diode Conduction)[a, b]		I_S	0.8		
Power Dissipation[a, b]	T_A= 25°C	P_D	0.96	0.7	W
	T_A= 70°C		0.6	0.45	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	–55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient[a]	t ≤ 5 sec	R_{thJA}	100	130	°C/W
	Steady State		140	175	
Maximum Junction-to-Foot (drain)	Steady State	R_{thJF}	60	75	

Notes
a. Surface Mounted on 1” x 1” FR4 Board.
b. Pulse width limited by maximum junction temperature

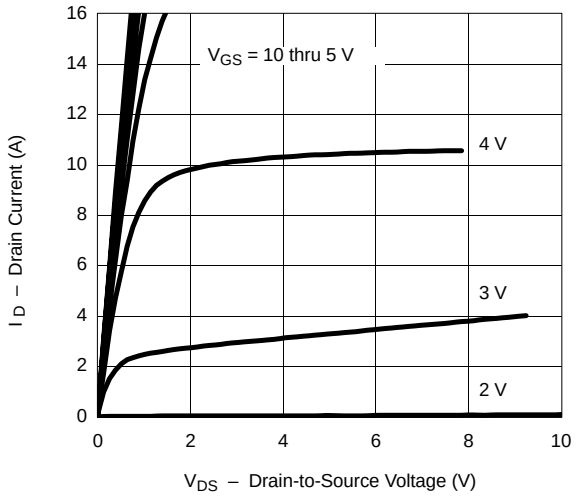
SPECIFICATIONS (T_A = 25°C UNLESS OTHERWISE NOTED)

Parameter	Symbol	Test Conditions	Limits Min	Limits Typ	Limits Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 µA	30			V
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	0.8			V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 24 V, V_{GS} = 0 V			0.5	µA
		V_{DS} = 24 V, V_{GS} = 0 V, T_J = 55°C			10	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} ≥ 4.5 V, V_{GS} = 10 V	6			A
On-State Drain Current[a]		V_{DS} ≥ 4.5 V, V_{GS} = 4.5 V	4			
Drain-Source On-Resistance[a]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 3.4 A		0.042	0.050	Ω
		V_{GS} = 4.5 V, I_D = 2.6 A		0.068	0.085	
Forward Transconductance[a]	g_{fs}	V_{DS} = 4.5 V, I_D = 3.4 A		6.0		S
Diode Forward Voltage	V_{SD}	I_S = 0.8 A, V_{GS} = 0 V		0.8	1.2	V
Dynamic[b]						
Total Gate Charge	Q_g	V_{DS} = 15 V, V_{GS} = 10 V, I_D = 3.4 A		4.3	7	nC
Gate-Source Charge	Q_{gs}			0.65		
Gate-Drain Charge	Q_{gd}			1.2		
Input Capacitance	C_{iss}	V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz		215		pF
Output Capacitance	C_{oss}			90		
Reverse Transfer Capacitance	C_{rss}			55		
Switching						
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 15 V, R_L = 15 Ω I_D ≅ 1.0 A, V_{GEN} = 10 V, R_G = 6 Ω		9	15	ns
Rise Time	t_r			9	15	
Turn-Off Delay Time	$t_{d(off)}$			14	20	
Fall-Time	t_f			6	12	

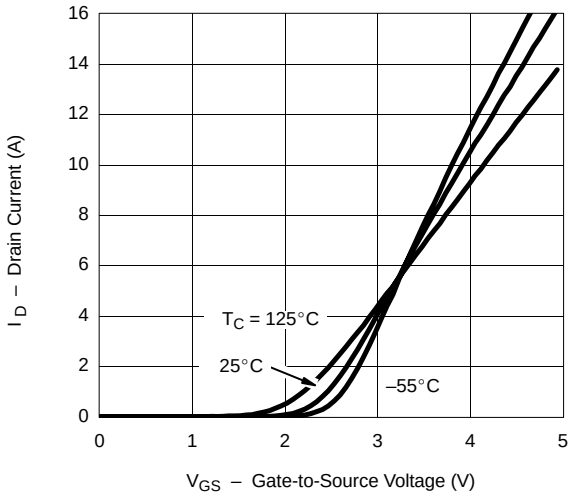
Notes
a. Pulse test: PW ≤300 µs duty cycle ≤2%.
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

Output Characteristics

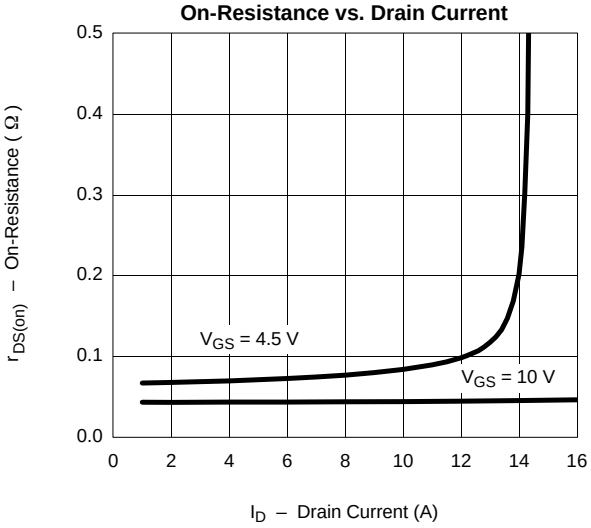


Transfer Characteristics

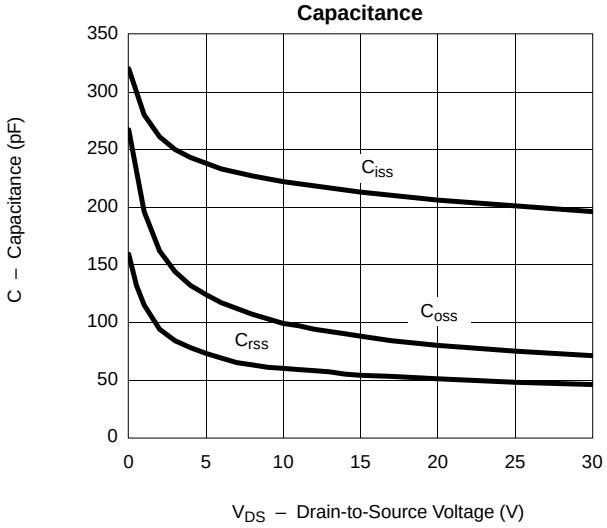


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

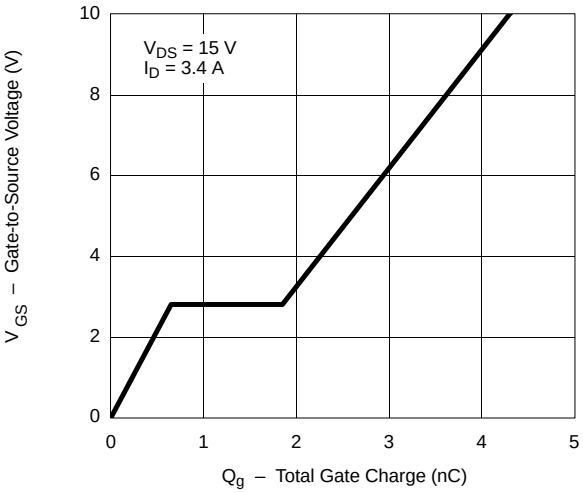
On-Resistance vs. Drain Current



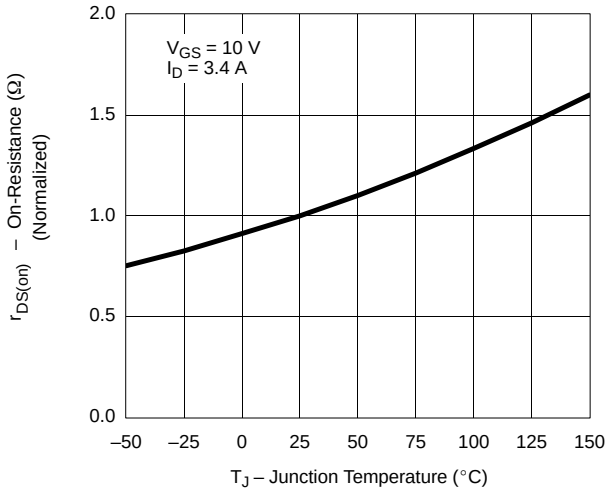
Capacitance



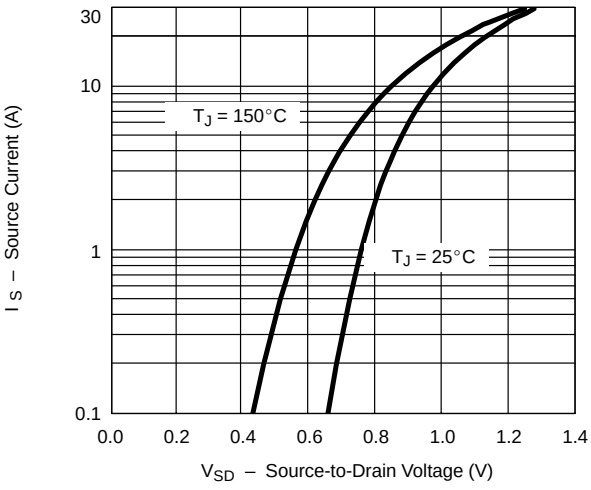
Gate Charge



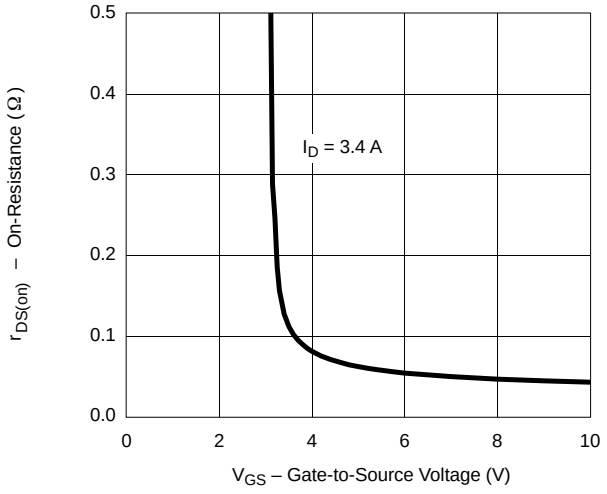
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage

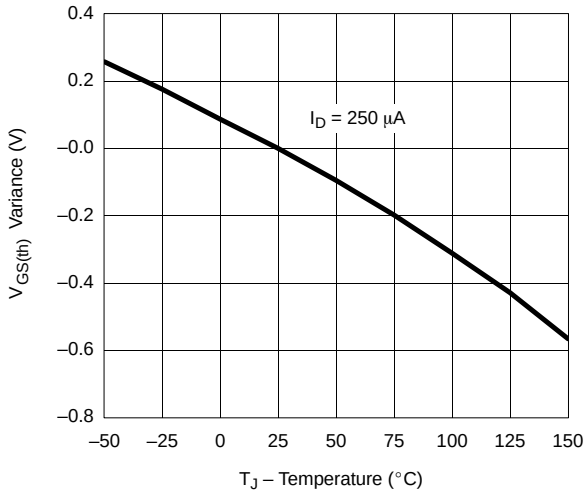


On-Resistance vs. Gate-to-Source Voltage

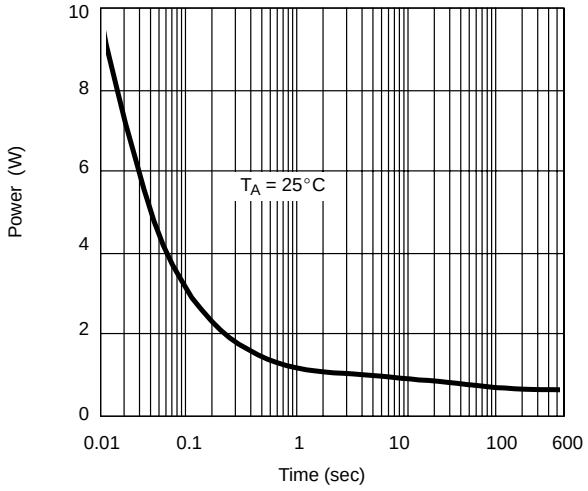


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient